

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20180112000 Transfer of select CS150/CS200 devices from GFAB to MAINEFAB Wafer Fab site Change Notification / Sample Request

Date: January 22, 2018

To: TOKYO ELECTRON DEVICE (DSTR) PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN www admin team@list.ti.com).

PCN Team SC Business Services

20180112000 Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICE	CUSTOMER PART NUMBER
DS26C32ATM/NOPB	null
DS26C32ATMX/NOPB	null
DS26LV31TM/NOPB	null
DS26LV32ATM/NOPB	null
DS34C86TM/NOPB	null
DS26C31TM/NOPB	null
DS26C31TMX/NOPB	null
DS26LV31TMX/NOPB	null
DS26LV32ATMX/NOPB	null
DS34LV86TM/NOPB	null
DS34C87TMX/NOPB	null
DS34LV86TMX/NOPB	null
DS34LV87TMX/NOPB	null
DS34LV87TM/NOPB	null
DS89C21TM/NOPB	null
DS34C87TM/NOPB	null
DS89C21TMX/NOPB	null
DS34C86TMX/NOPB	null

Technical details of this Product Change follow on the next page(s).

PCN Number: 20180112000				12000			PCN D)a	te:	Jan 22	, 2018		
Title: Transfer of select CS150/CS200 dev				vices from G	FAE	3 to MA	ΙN	EF	AB Wafer Fa	ab site			
Cus	stom	er Contact:		PC	N Manager			Dept:				Services	
Pro	pose	d 1 st Ship Da	te:	An	r 22, 2018			ated Sa	m	pl		rovided at	
				٦.٣		Ava	<u>aila</u>	bility:			sample	request.	
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H	Desi	embly Site			Assembly F	pecification			F	╣	Assembly Mochanical	Specificatio	n
H		: Site		Ħ		ipping/Labe	lina	1	F	┪	Test Proces		11
H		er Bump Site			Wafer Bum		iiiig			11	Wafer Bum		
X		er Fab Site		X	Wafer Fab				\overline{X}	1	Wafer Fab	•	
					Part number								
						l Details		•					
Des	script	tion of Chang	e:										
		nge notification B Wafer Fab s	ite for the						t /		ected" secti		:he
			rrent			61 : 63				ev			_
	hip ite	Process	Wafer Diamete	r	Interlayer Dielectric	Chip Site		Proces	S		Wafer Diameter	Interlayer Dielectric	
	AB6	CS150/CS200	150mm		TEOS	MAINEFAB*	С	S150/CS	520	00	200mm	TEOS	1
					Base ILD							CMP	
					TEOS								
					SOG/ SOG								
					etchback								
GF	AB8	CS150/CS200	200mm		TEOS	MAINEFAB*	С	S150/CS	520	00	200mm	TEOS	1
					Base ILD							CMP	
					TEOS								
					SOG/ SOG								
					etchback								
	hip ite	Process	Wafer Diamete	er	Contact Plug	Chip Site		Proces	S		Wafer Diameter	Contact Plug	
	AB6	CS150/CS200	150mm	_	Part of metallization	MAINEFAB*	С	S150/CS	520	00	200mm	W plug	
GF	AB8	CS150/CS200	200mm		Part of	MAINEFAB*	С	S150/CS	520	00	200mm	W plug	1
					metallization								
Che Qua	emical	er Dielectric (1 -Mechanical Plails are provide for Change:	lanárizati	on	(CMP) ILD ar	nd Tungsten							ed
GFA	GFAB closure												
Ant	ticipa	ted impact o	n Form,	Fit	, Function,	Quality or	Reli	iability	(1	00	sitive / ne	gative):	
					-						•		

Changes to product identification resulting from this PCN:

Current:

Current Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
GFAB6	GF6	GBR	Greenock
GFAB8	GF8	GBR	Greenock

New Fab Site:

New Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City
MAINEFAB	CUA	USA	South Portland

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS

MADE IN: Malaysia
2DC: 20:

MSL '2 /260C/1 YEAR SEAL DT
MSL 1 /235C/UNLIM 03/29/04

OPT:
ITEM: 39

LBL: 5A (L) T0:1750



(1P) \$N74L\$07N\$R

(Q) 2000 (D) 0336

(31T)LOT: 3959047MLA

(4W) TKY(1T) 7523483\$I2

(P)

(2P) REV:
(20L) CSO: SHE (21L) CCO: USA
(22L) ASO: MLA (23L) ACO: MYS

Product Affected:

L	Product Affected:			
	ADC10738CIWM/NOPB	DS26C31TMX/NOPB	DS34C86TMX/NOPB	DS89C21TM/NOPB
	ADC10738CIWMX/NOPB	DS26C32ATM/NOPB	DS34C87TM/NOPB	DS89C21TMX/J7002999
	DP8570AV/NOPB	DS26C32ATMX/NOPB	DS34C87TMX/NOPB	DS89C21TMX/NOPB
	DP8570AVX/NOPB	DS26LV31TM/NOPB	DS34LV86TM/NOPB	LM12458CIV/NOPB
	DP8573AV/NOPB	DS26LV31TMX/NOPB	DS34LV86TMX/NOPB	LM12458CIVX/NOPB
	DP8573AVX/NOPB	DS26LV32ATM/NOPB	DS34LV87TM/NOPB	LM12H458CIV/NOPB
	DP8573A-W	DS26LV32ATMX/NOPB	DS34LV87TMX/NOPB	SCL1033-V0/E7001896
	DS26C31TM/NOPB	DS34C86TM/NOPB		

Qualification Report

MAINEFAB CS200 Technology Qualification Approve Date 21-Dec-2017

Product Attributes

Attributes	Qual Device: <u>ADC10664CIWMNOPB_QL</u>
Assembly Site	AMKOR AP1
Package Family	SOIC
Wafer Fab Supplier	MAINEFAB
Wafer Fab Process	CS200

⁻ QBS: Qual By Similarity

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: ADC10664CIWM/NOPB
AC	Autoclave 121C	96 Hours	3/240/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/240/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/240/0
ELFR	Early Life Failure Rate, 125C	48 Hours	3/2400/0
HTOL	Life Test, 125C	1000 Hours	3/240/0
HTSL	High Temp Storage Bake 150C	1000 Hours	3/240/0
HBM	ESD - HBM	2500 V	3/9/0
CDM	ESD - CDM	500 V	3/9/0
LU	Latch-up	(per JESD78)	3/18/0
ED	Electrical Characterization	Per Datasheet Parameters	3/90/0
MQ	Assembly MQ	-	Passed
MQ	Wafer FAB MQ	-	Passed

⁻ Preconditioning was performed for Auto dave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- $The following are equivalent HTSL \ options \ based on an activation energy of 0.7 eV: 150 C/1 k \ Hours, and 170 C/420 \ Hours \ Archive the following are equivalent HTSL options based on an activation energy of 0.7 eV: 150 C/1 k \ Hours, and 170 C/420 \ Hours \ Hours$

- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

Qualification Report CS150 Technology Qualification - MFAB

Approve Date 21-July-2017

Product Attributes

Attributes	Qual Device: ADC12138CIMSA/NOPB
Assembly Site	AMKOR AP1
Package Family	SSOP
Wafer Fab Supplier	MAINEFAB
Wafer Fab Process	CS150

⁻ QBS: Qual By Similarity

⁻ Qual Device ADC10664CIWWNOPB is qualified at LEVEL3-260C

⁻ Qual Device ADC12138CIMSA/NOPB is qualified at LEVEL3-260C

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	Test Name / Condition	Duration	Qual Device: ADC12138CIMSA/NOPB
AC	Autoclave 121C	96 Hours	3/231/0
HAST	Biased HAST, 130C/85%RH	96 Hours	3/231/0
TC	Temperature Cycle, -65/150C	500 Cycles	3/231/0
ELFR	Early Life Failure Rate, 125C	48HRS	3/2400/0
HTOL	Life Test, 125C	1000 Hours	3/231/0
HTSL	High Temp Storage Bake 150C	1000 Hours	3/231/0
НВМ	ESD - HBM - Q100	1500 V	3/9/0
CDM	ESD - CDM - Q100	500 V	3/9/0
LU	Latch-up	(Per JESD78)	3/18/0
ED	Electrical Characterization	Per Datasheet Parameters	3/90/0
MQ	Manufacturability (Assembly)	(per mfg. Site specification)	Pass
MQ	Manufacturability (Wafer Fab)	(per mfg. Site specification)	Pass

⁻ Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable

- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

Green/Pb-free Status:

Qualified Pb-Free (SMT) and Green

For questions regarding this notice, e-mails can be sent to the regional contacts shown below, or you can contact your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com